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Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0035			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0042			
I <sub>D</sub> (A)	50			
Configuration	Single			

TO-252

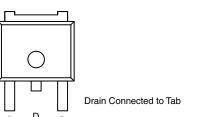
Top View

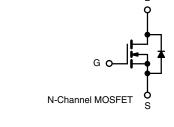
#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization:
   For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



FREE





ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50N04-3m5L-GE3			

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	40	V		
Gate-Source Voltage		V <sub>GS</sub>	± 20			
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	I <sub>D</sub>	50			
	T <sub>C</sub> = 125 °C		50			
Continuous Source Current (Diode Conduction) <sup>a</sup>		Is	50	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	200			
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	55			
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	151	mJ		
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	136	W		
	T <sub>C</sub> = 125 °C		45	VV		
Operating Junction and Storage Temperature Range	е	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	C/W	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							,	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		-	2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0029	0.0035	Ω	
Drain-Source On-State Resistance <sup>a</sup>	Б	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0056		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0068		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 20 A	-	0.0034	0.0042		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		105	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	4880	5860	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	560	670		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	250	300		
Total Gate Charge <sup>c</sup>	Qg			-	85	130		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 50 \text{ A}$	-	14	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	]		-	14	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1	2	3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	11		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_L = 0.4 \Omega$ $I_D \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	11	14	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	39	47		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	11	14		
Source-Drain Diode Ratings and Chara	icteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V		_	0.9	1.5	V	

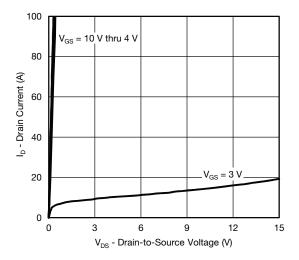
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

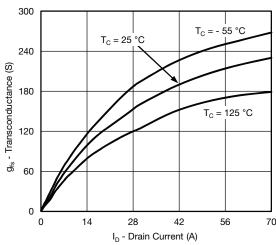
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



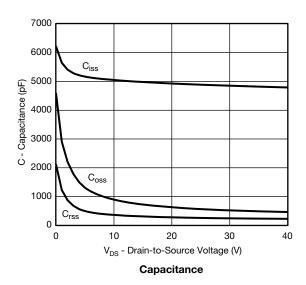
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

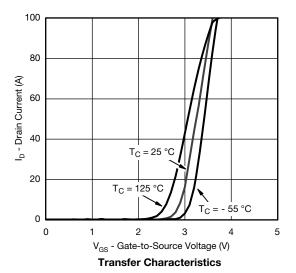


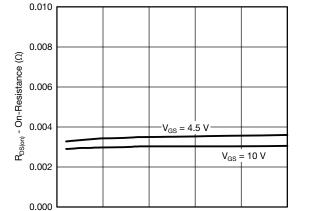
### **Output Characteristics**



Transconductance







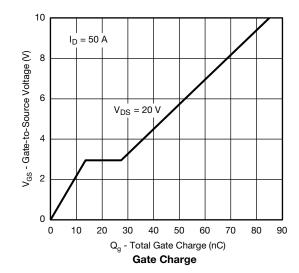
I<sub>D</sub> - Drain Current (A)

On-Resistance vs. Drain Current

80

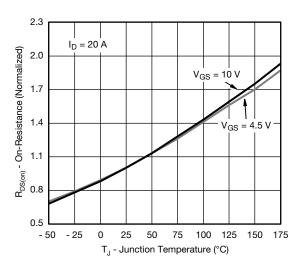
100

0

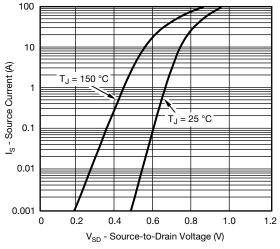




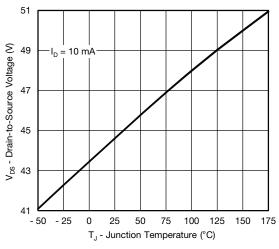
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



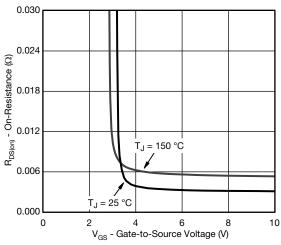
#### On-Resistance vs. Junction Temperature



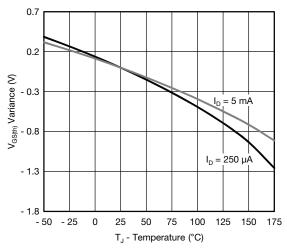
**Source Drain Diode Forward Voltage** 



Drain Source Breakdown vs. Junction Temperature



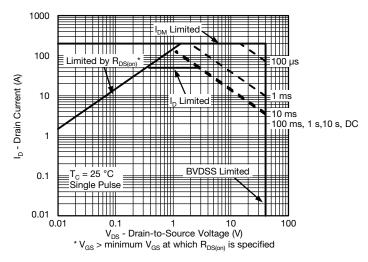
On-Resistance vs. Gate-to-Source Voltage



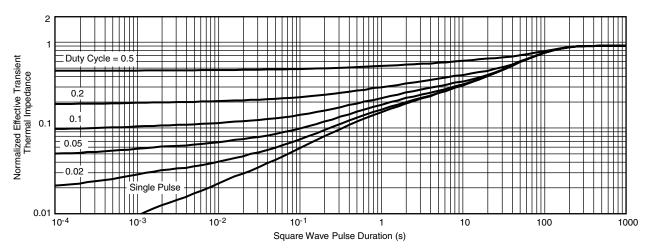
**Threshold Voltage** 



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



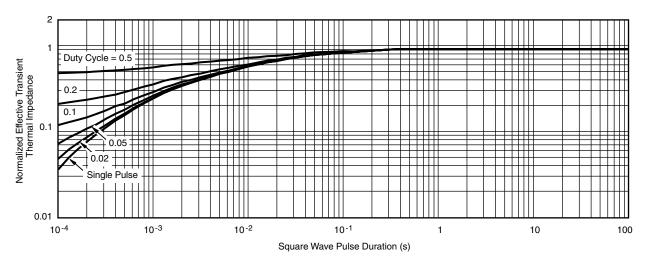
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

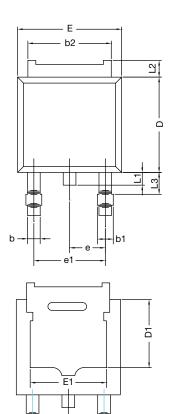
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

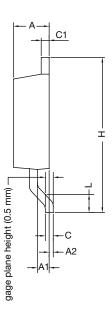
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg263751">www.vishay.com/ppg263751</a>.



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### **TO-252AA CASE OUTLINE**





	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Η	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

#### Note

· Dimension L3 is for reference only.

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### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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